

CMLDM8005
SURFACE MOUNT SILICON
DUAL P-CHANNEL
ENHANCEMENT-MODE
MOSFET



SOT-563 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM8005 consists of dual P-Channel enhancement-mode silicon MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low $r_{DS(ON)}$ and low threshold voltage.

MARKING CODE: CC8

FEATURES:

- ESD protection up to 1800V (Human Body Model)
- 350mW power dissipation
- Very low $r_{DS(ON)}$
- Low threshold voltage
- Logic level compatible
- Small, SOT-563 surface mount package
- Complementary dual N-Channel device: CMLDM7005

APPLICATIONS:

- Load switch/Level shifting
- Battery charging
- Boost switch
- Electro-luminescent backlighting

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage	
Gate-Source Voltage	
Continuous Drain Current (Steady State - Note 1)	
Continuous Source Current (Body Diode)	
Maximum Pulsed Drain Current	
Power Dissipation (Note 1)	
Power Dissipation (Note 2)	
Power Dissipation (Note 2)	
Operating and Storage Junction Temperature	
Thermal Resistance (Note 1)	

SYMBOL		UNITS
V_{DS}	20	V
V_{GS}	8.0	V
I_D	650	mA
I_S	250	mA
I_{DM}	1.0	A
P_D	350	mW
P_D	300	mW
P_D	150	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=4.5\text{V}, V_{DS}=0$			10	μA
I_{DSS}	$V_{DS}=16\text{V}, V_{GS}=0$			100	nA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.5		1.0	V
V_{SD}	$V_{GS}=0, I_S=250\text{mA}$			1.1	V
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=350\text{mA}$		0.25	0.36	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=300\text{mA}$		0.37	0.5	Ω
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=150\text{mA}$			0.8	Ω

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

CMLDM8005

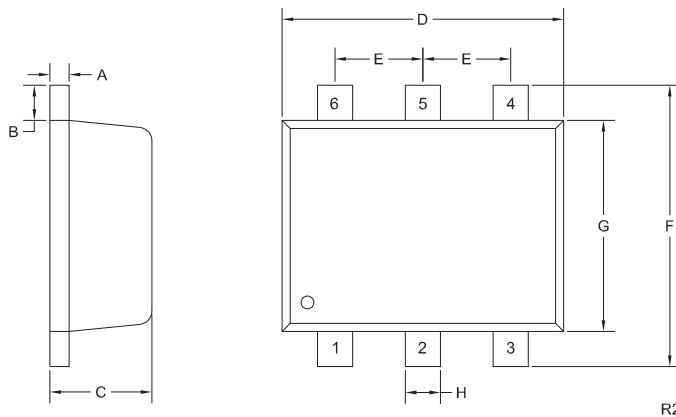
**SURFACE MOUNT SILICON
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ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	UNITS
g_{FS}	$V_{DS}=10\text{V}, I_D=200\text{mA}$	0.2		S
C_{rSS}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$		25	pF
C_{iss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$		100	pF
C_{oss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$		21	pF
$Q_{g(\text{tot})}$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$		1.2	nC
Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$		0.24	nC
Q_{gd}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$		0.36	nC
t_{on}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}, R_G=10\Omega$		38	ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}, R_G=10\Omega$		48	ns

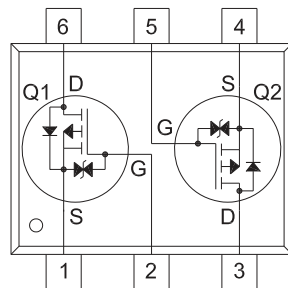
SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R2)

PIN CONFIGURATION



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

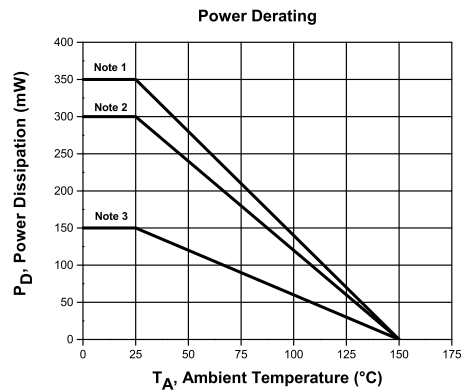
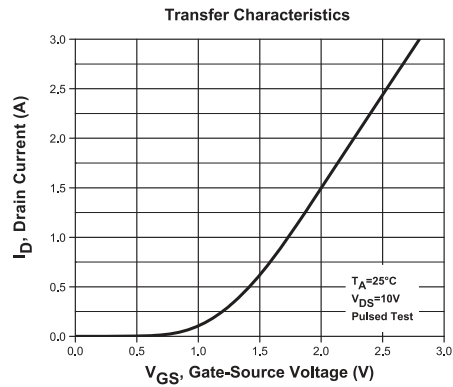
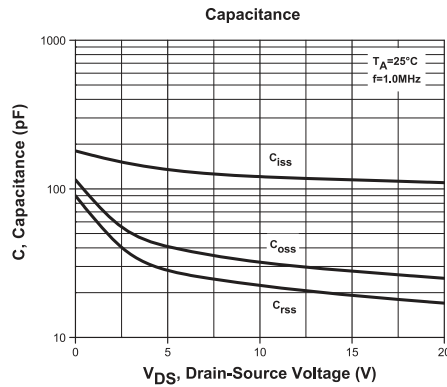
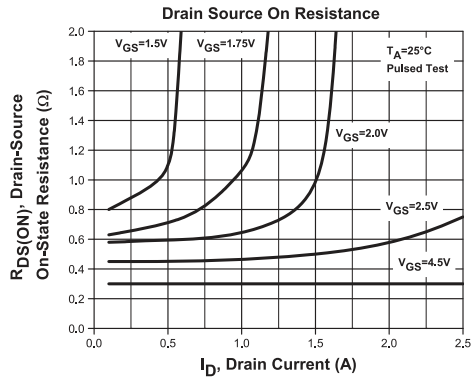
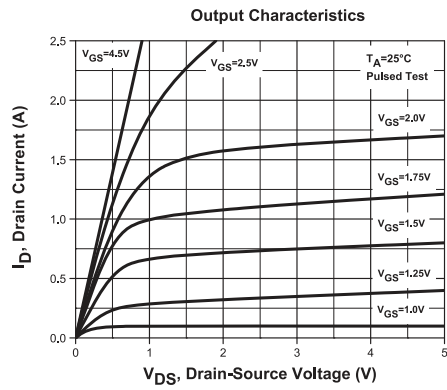
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R6 (8-June 2015)

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TYPICAL ELECTRICAL CHARACTERISTICS



R6 (8-June 2015)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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